

N-Channel 120 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	V _{DS} (V) R _{DS(on)} (mΩ)(Typ.)		Q _g (Typ.)				
120	3 at V _{GS} = 10 V	210	145 nC				

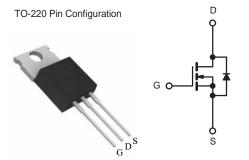


FEATURES

- DT-SJ Power MOSFET
- 100 % Rg and UIS tested
- Green Device Available

APPLICATIONS

- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	120	V				
Gate-Source Voltage	V _{GS}	V _{GS} ± 20					
Continuous Drain Current (T,I = 150 °C)	T _C = 25 °C	I-	210	Δ.			
Continuous Drain Current (1) = 150 C)	T _C = 100 °C	I _D	135				
Pulsed Drain Current (t = 100 μs)	I _{DM}	840	А				
Avalanche Current L = 0.1 mH		I _{AS}	190				
ingle Avalanche Energy ^a		E _{AS}	570	mJ			
Maximum Power Dissipation ^a	T _C = 25 °C	В	362	W			
Maximum Fower Dissipation 4	T _C = 125 °C	$ P_D$	253				
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +150	°C				

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	58	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.35	C/VV			

Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

Rev. 1. 0



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	120	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V	-	-	1	μΑ
Zero date voltage Drain ourient	IDSS	V _{DS} = 96 V, V _{GS} = 0 V, T _J = 100 °C	-	-	100	
Drain-Source On-State Resistance a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	3	3.6	mΩ
Forward Transconductance a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_D = 20 \text{ A}$	-	75	-	S
Dynamic ^b				•		
Input Capacitance	C _{iss}		-	9200	-	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 60 \text{ V}, f = 1 \text{ MHz}$	-	761	-	
Reverse Transfer Capacitance	C _{rss}		-	3	-	
Total Gate Charge ^c	Qg		-	145	-	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	56	-	
Gate-Drain Charge ^c	Q_{gd}		-	52	-	
Gate Resistance	R_g	f = 1 MHz	-	2.5	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	30	-	ns
Rise Time ^c	t _r	$V_{DD} = 60 \text{ V}, R_L = 1.67 \Omega$	-	55	-	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D = 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	90	-	
Fall Time ^c	t _f		-	42	-	
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)				
Continuous Source Current	I _S	$T_C = 25 ^{\circ}C$	-	-	210	Α
Pulsed Current (t = 100 μs)	I _{SM}		-	-	840	Α
Forward Voltage ^a	V_{SD}	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.2	V
Reverse Recovery Time	t _{rr}	1 00 A di/d+ 100 A/··-	-	28	-	ns
Reverse Recovery Charge	Q _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	110	-	nC

Notes

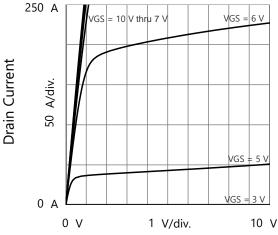
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

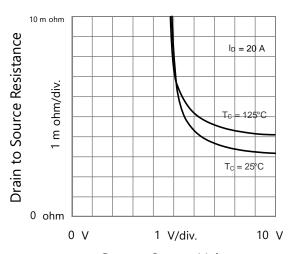




TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

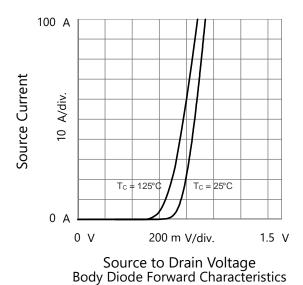


Drain to Source Voltage Output Characteristics



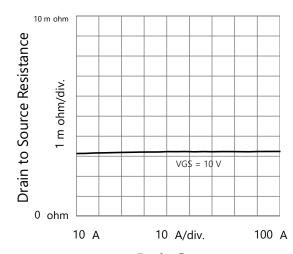
Gate to Source Voltage

Drain to Source Resistance vs. Gate to Source Voltage



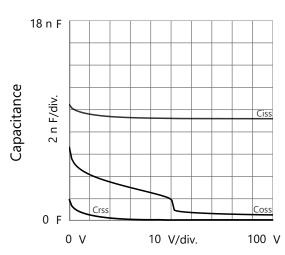
O V 1 V/div. 10 V

Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

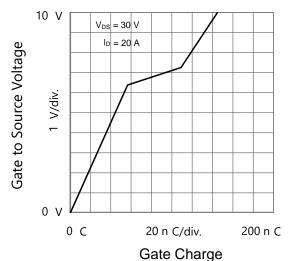
Transfer Characteristics



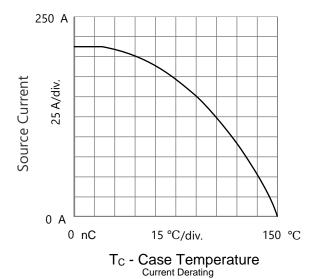
Drain to Source Voltage Capacitances

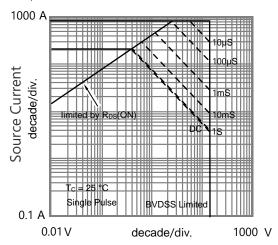
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TYPICAL CHARACTERISTICS (T = 25 °C, unless otherwise noted)

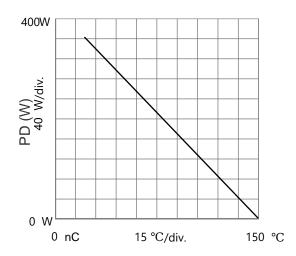


Gate to Source Voltage vs. GateCharge





Source to Drain Voltage Safe Operating Area, Junction-to-Ambient

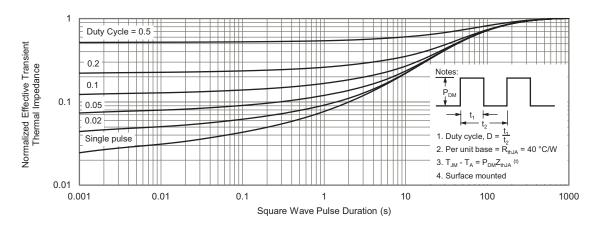


T_C - Case Temperature

Power Derating



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

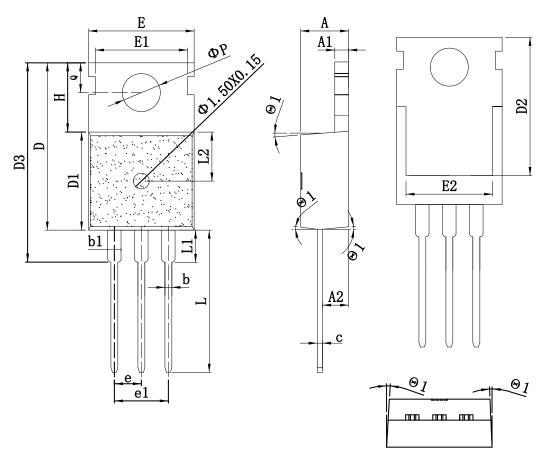
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



TO-220_3L-A PACKAGE OUTLINE

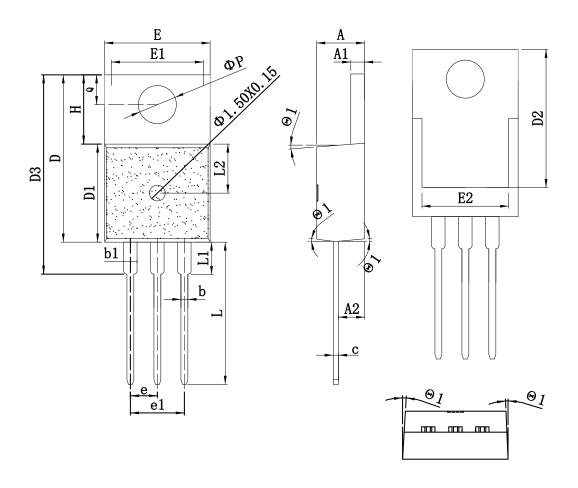


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
SIMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

CVMDOI	mm			CVMDOI	mm		
SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
ь	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°





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